
X-band Structure Design For The NLC

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Design Considerations

- Emittance preservation, tolerance specs – wakefield suppression
 - Short-range wakefields $\propto a^{-3.8}$: set lower limit on aperture: $a \cong 0.18\lambda$
 - Long-range wakefields: mode detuning and damping
- Minimizing surface field
- Reducing breakdown damage
- Minimizing RF pulse heating
- Cost effective
- ...

Continuing Improvements

- Breakdown problems with 1.8m structure (RDDS, DDS)
 - Low achievable gradient
 - Severe damage, large frequency shift
- C.Adolphsen theory

$$- \cdot \frac{G^2 v_g^2}{(R/Q)^2} \frac{\sin(\phi)}{\phi \sin(\phi) + 2v_g \cos(\phi)}$$

- Low v_g or low RF power/structure
- Structure design approach
 - Traveling: $v_g/c \sim 3-5\%$
 - Standing wave: $v_g=0$

Low v_g With Large Aperture

- Traveling wave
 - Magnetic coupling (rf heating?)
 - High phase advance (bandwidth?)
- Standing wave (short length)

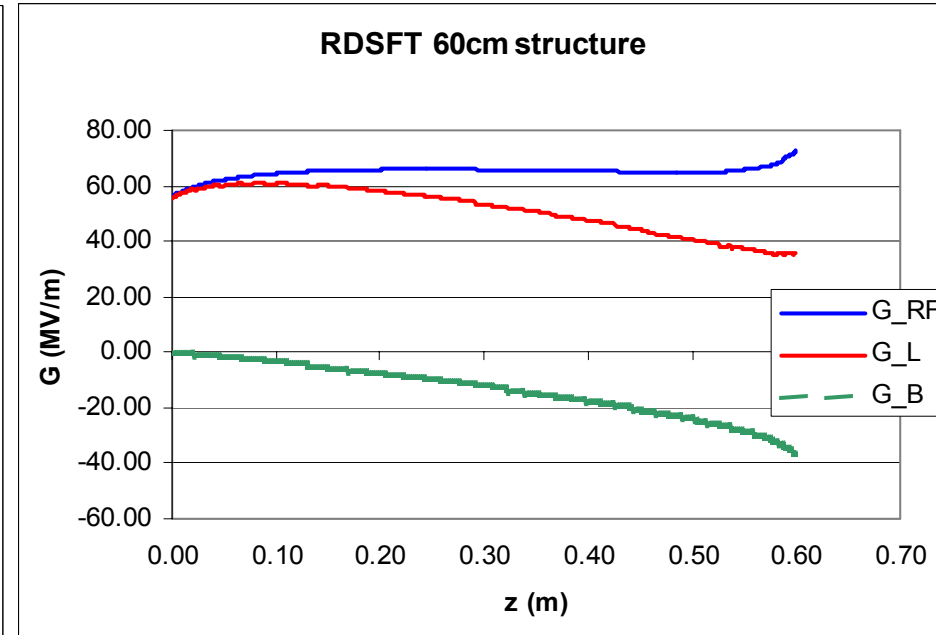
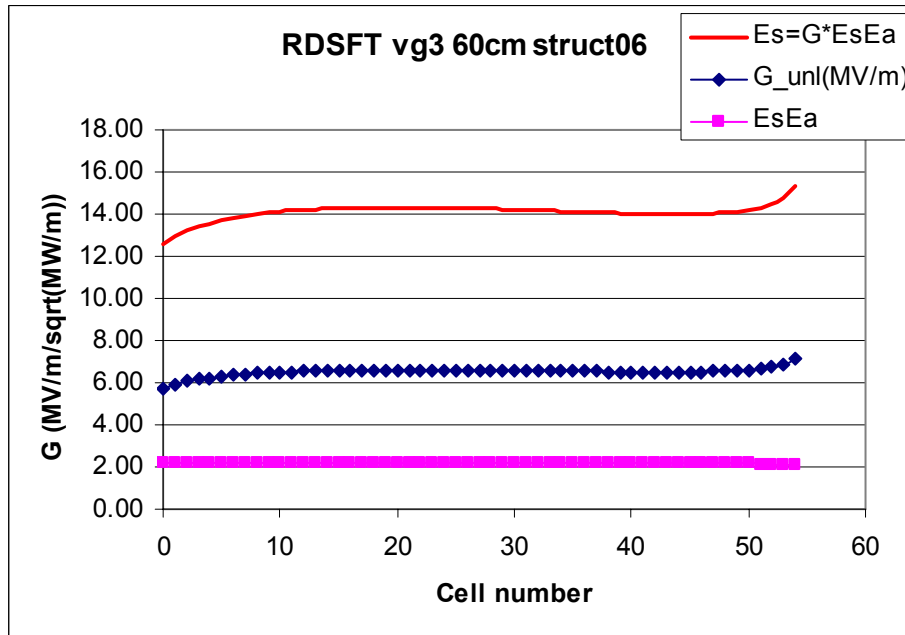
Traveling Wave Approach

High Phase Advance – $150^\circ/\text{cell}$

- With $\Phi=150^\circ$, one can
 - reduce v_g
 - maintain large aperture
 - maintain good rf efficiency
- Shorter length due to low v_g
- Low input power per structure
- Low surface field

H60VG3 Structure

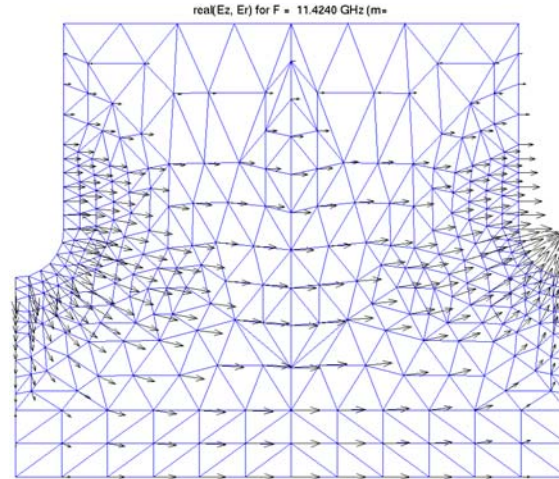
T_{fill} (ns)	110
τ	0.54
P_{RF} (MW)	58.85
I (A)	0.9
G_{RF} (MV/m)	65.0
G_{B}	-13.8
G_{L}	51.0



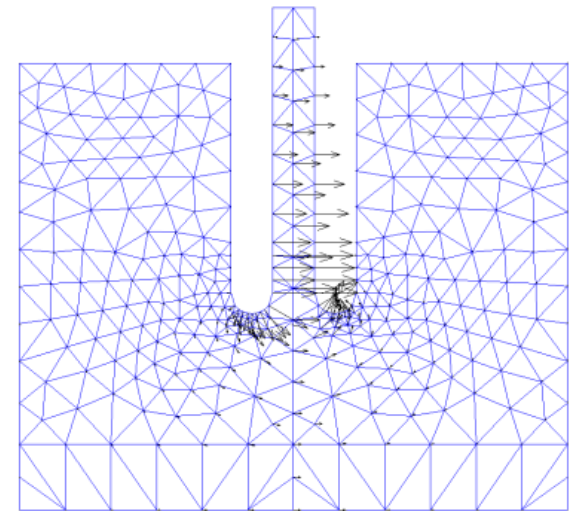
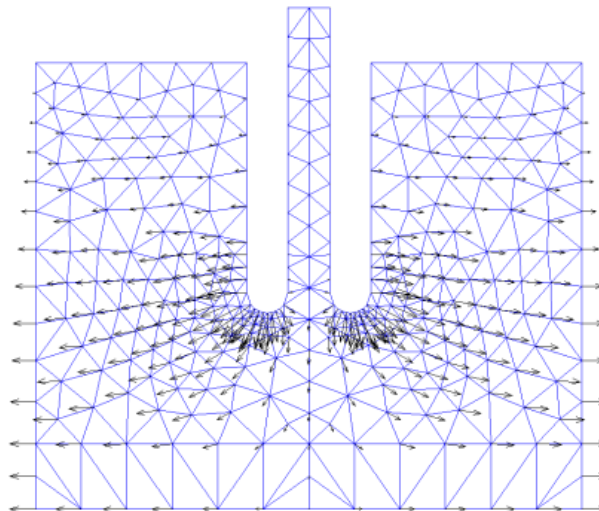
Standing Wave Approach

PI-mode vs PI/2 Bi-periodic

PI-mode

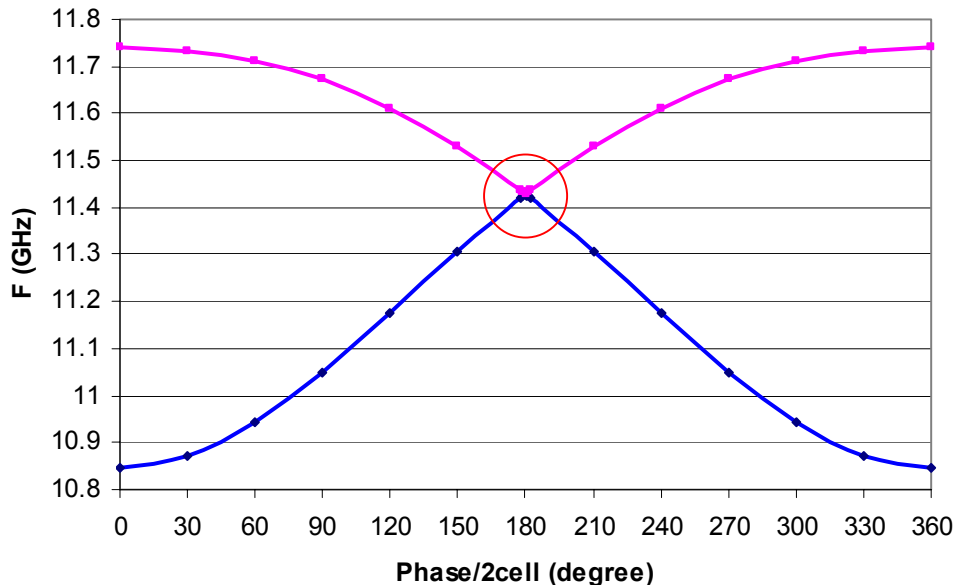


PI/2-mode



Bi-periodic Structure $m=0$ Mode

Bi-periodic Structure, $a=4.7\text{mm}$

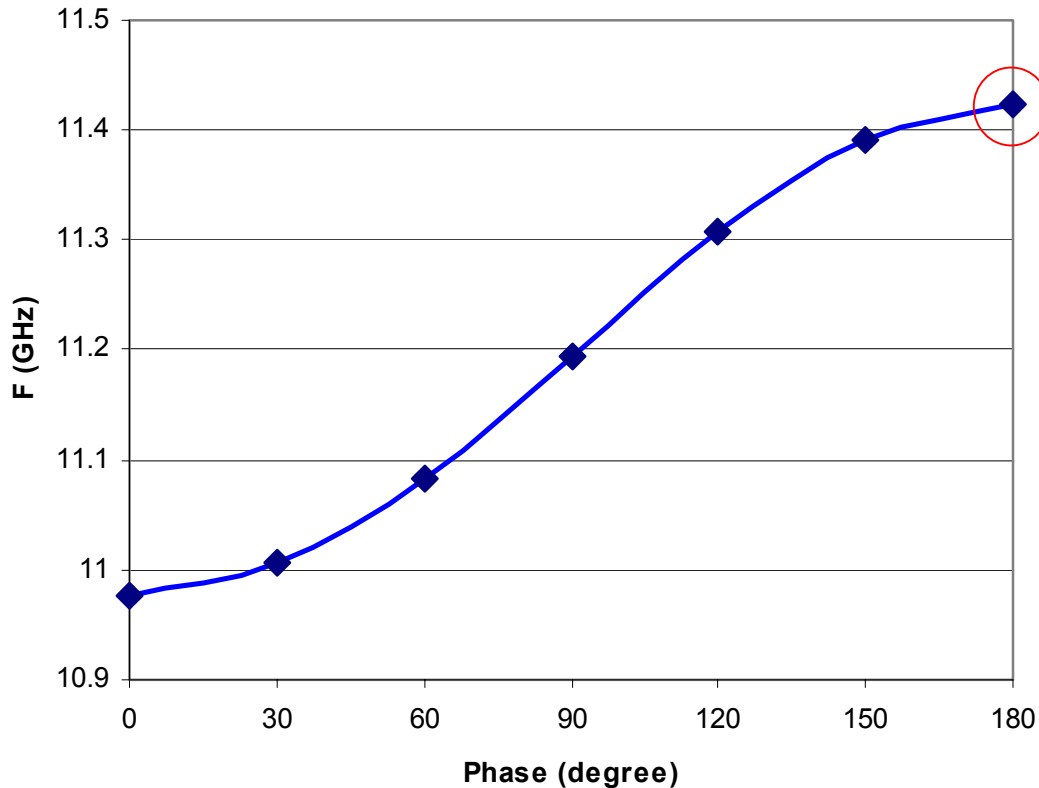


$A = 4.7\text{mm}$
 $F = 11.424\text{ GHz}$
 $Q = 8463$
 $R = 70.2\text{ M}\Omega/\text{m}$
 $R/Q = 8291$
 $E_s/E_a = 3.314$

- Large mode separation, can be longer in length
- Major concern - multi-pactoring in coupling cell
- Twice as many cells
- Efficient (with thin disk, but maybe high in E_s/E_a)

PI-mode SW Structure

PI-mode SW Structure, $a=4.75\text{mm}$

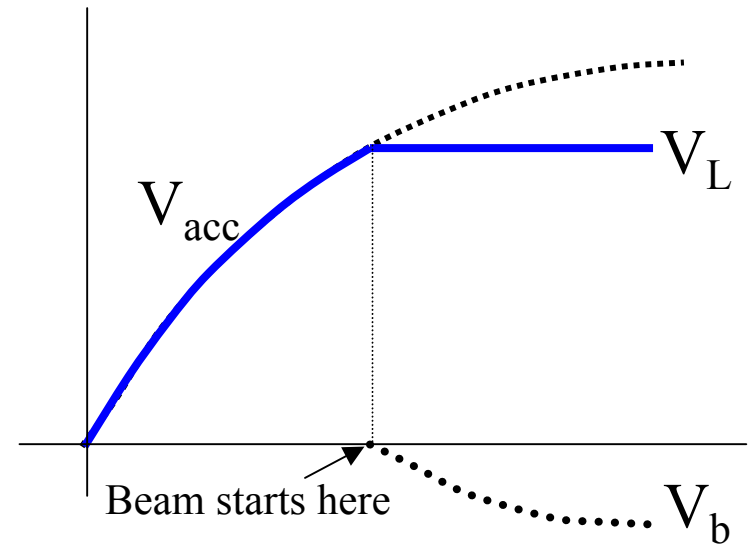


$A = 4.75 \text{ mm}$
 $F = 11.424 \text{ GHz}$
 $Q = 8820$
 $R = 68.0 \text{ M}\Omega/\text{m}$
 $R/Q = 7710$
 $E_s/E_a = 2.646$

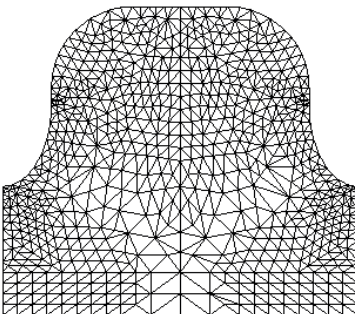
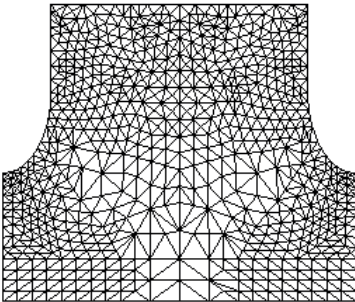
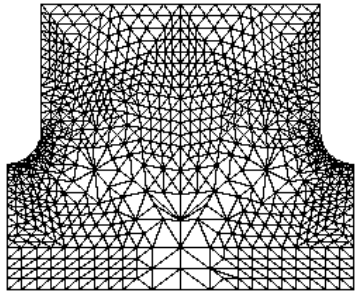
- Dense modes at PI
- Short structure length
- Low surface field with thick disk

Standing Wave Design

- PI-mode
- Short length
- Low input power and stored energy in structure
- Structure always operate at loaded gradient (55MV/m vs 70MV/m unloaded)
 - Coupling design for nominal current.
 - Adjust rf power at beam injection for different current



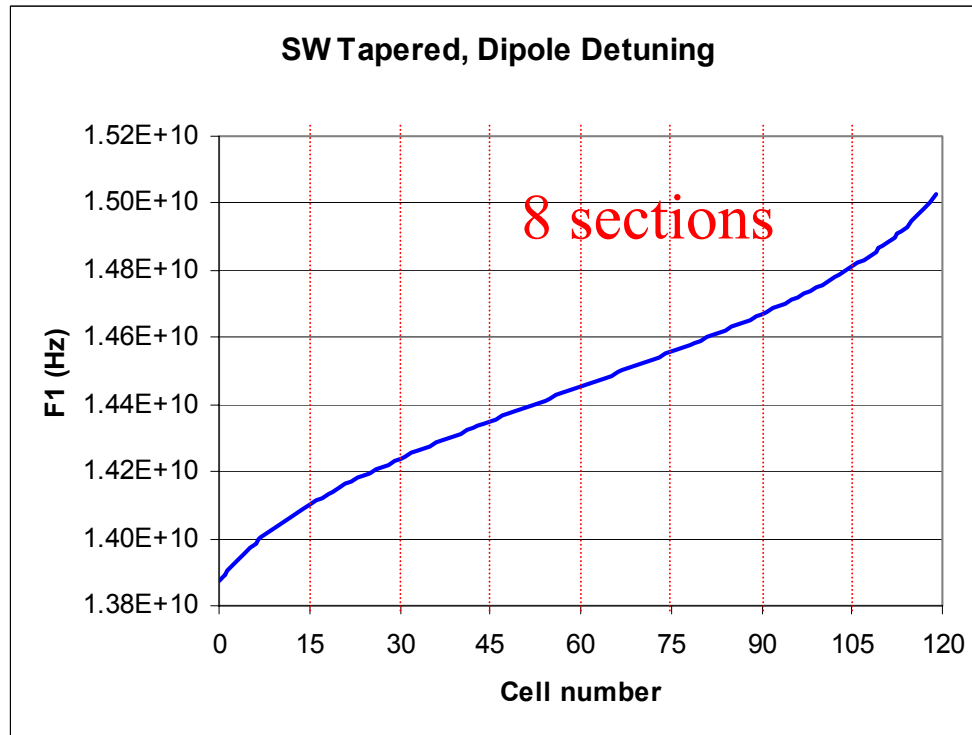
Cell Profile



	DLWG Thin T	Ellip iris Thick T	Round
A (mm)	4.75	4.75	4.75
T (mm)	2.6	3.6	3.6
R (M Ω /m)	67.7	64.2	71.7
R/Q	7742	7519	7478
Es/Ea	2.53	2.08	2.09

- PI mode
- Rounded cell
- Detuned
- Average a : 0.18λ
- Es/Ea designed to be about 2

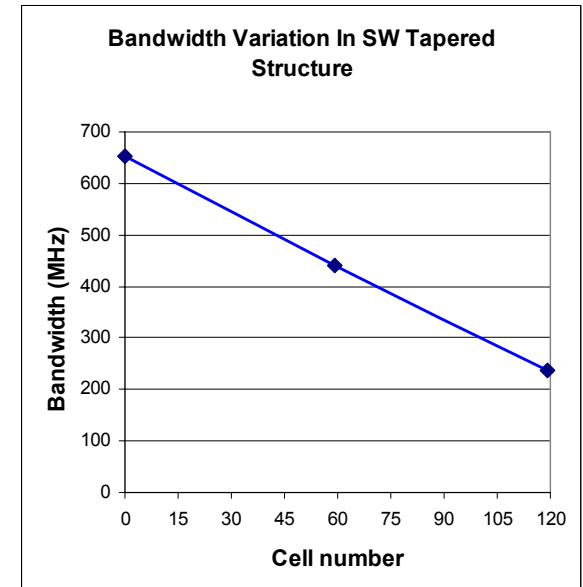
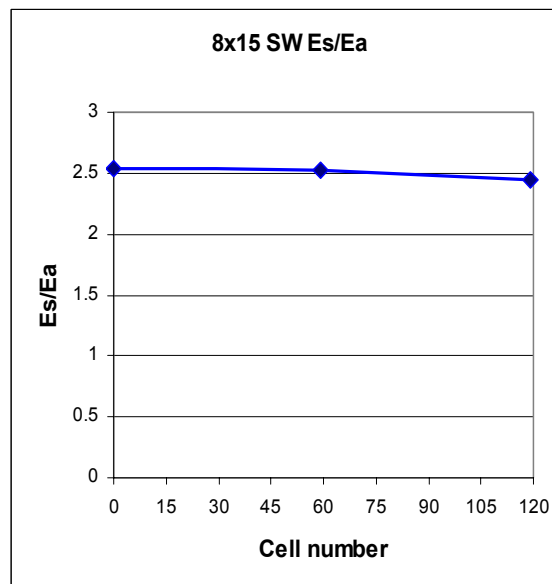
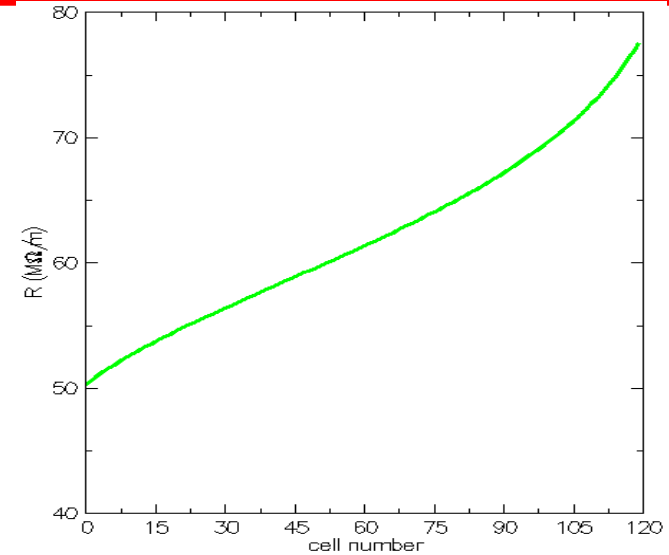
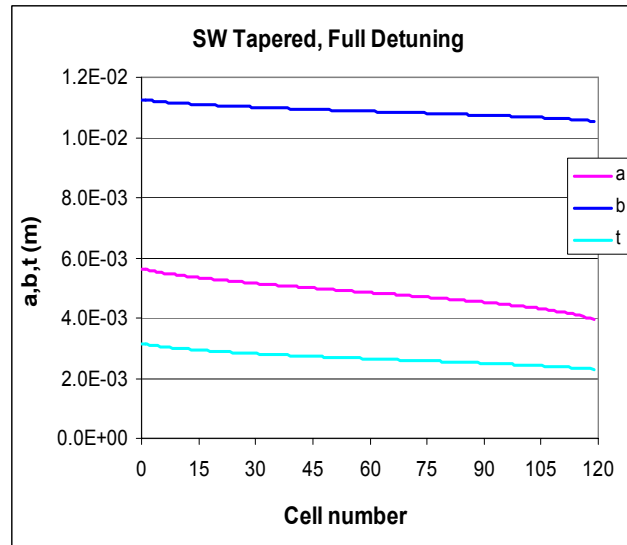
Dipole Mode Detuning



- Need similar detuning as TW $\Delta F_1 = 8 \sim 10\% / 4\sigma$
- Cannot detune within one structure
- Detune in 8 sections, 15 cells each (20cm)(not interleaved)
- 120 cells to detune full 8-10% spectrum

Tapered Structure Parameters (round iris)

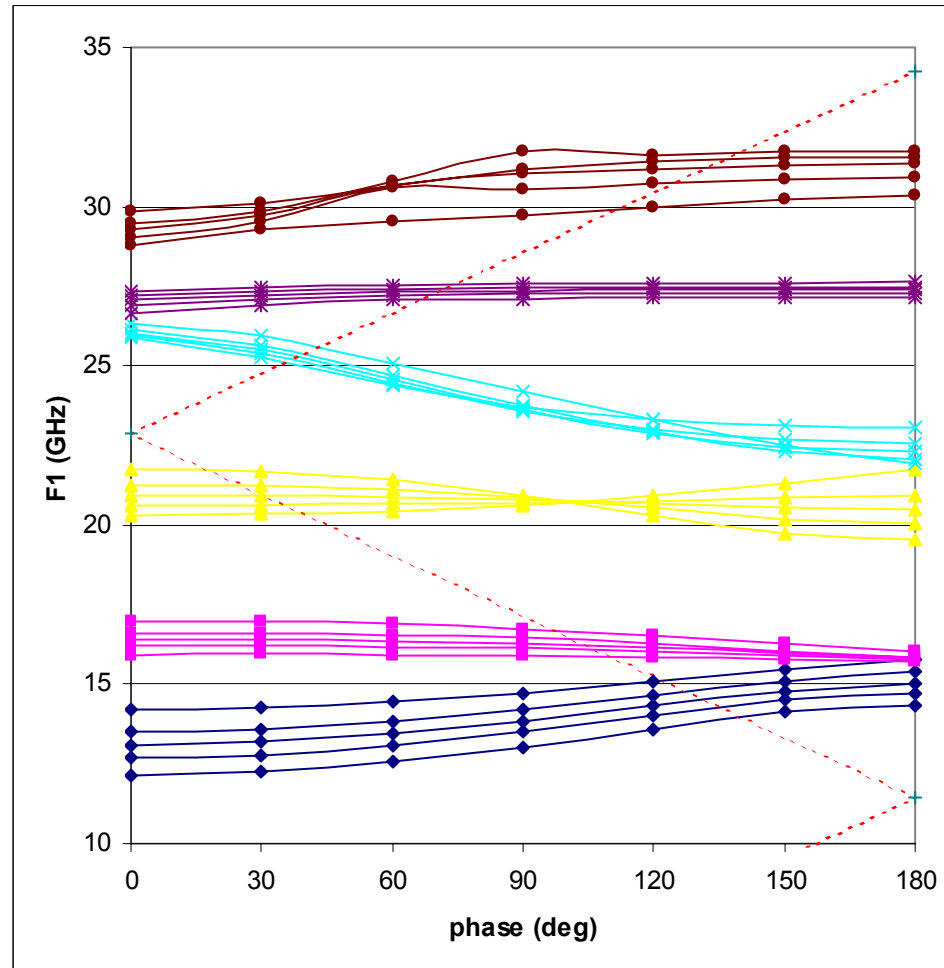
- Inverse taper in “t” for wider bandwidth at small “a”
- Adjust cell parameters to obtain flat field



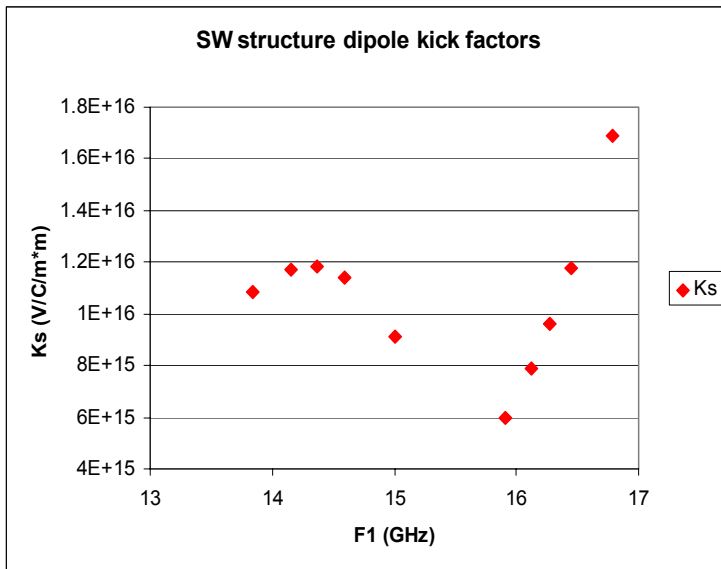
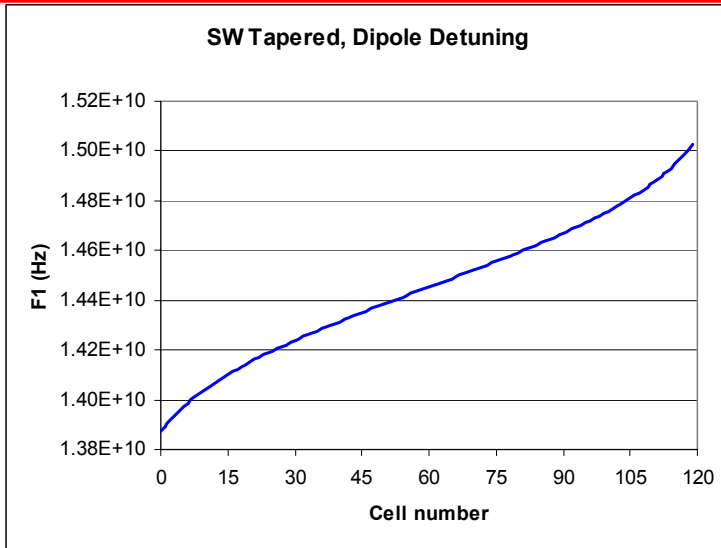
RF Parameters Of 8X15 Sections

	S1	S2	S3	S4	S5	S6	S7	S8
R(MΩ/m)	52.1	55.0	57.6	60.0	62.6	65.5	69.0	74.0
P(MW) for G=70MV/m	18.5	17.5	16.7	16.1	15.4	14.7	14.0	13.0
G(MV/m) for P=22MW	71.1	73.1	75.8	76.3	78.0	79.8	81.9	84.8

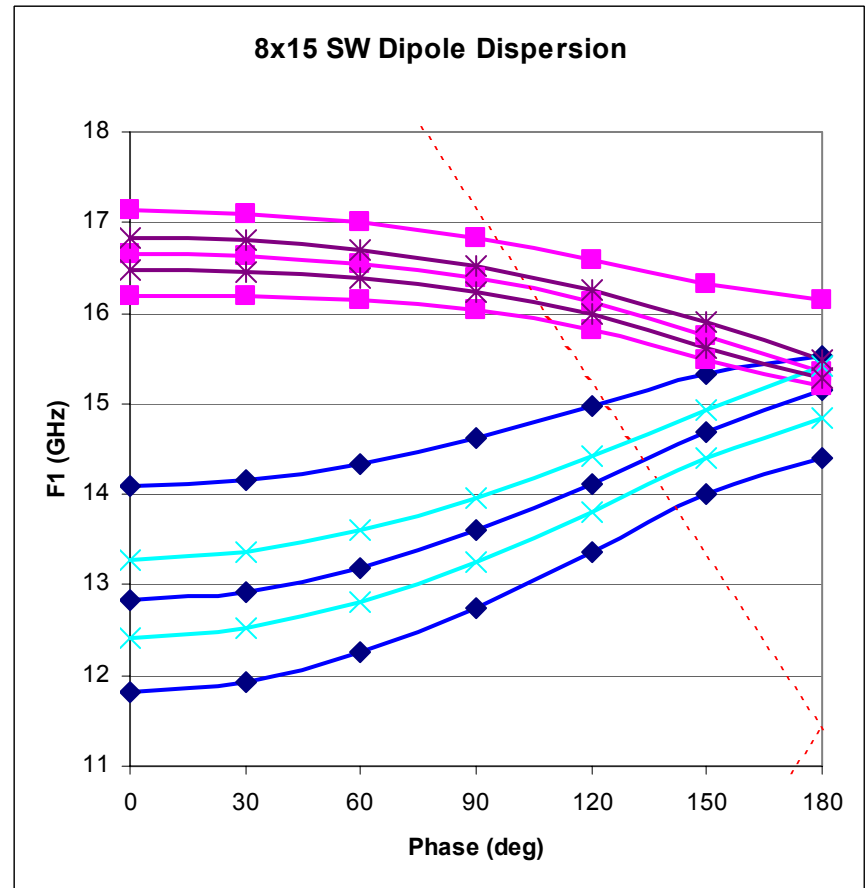
8X15 Detuned Dipole Dispersion



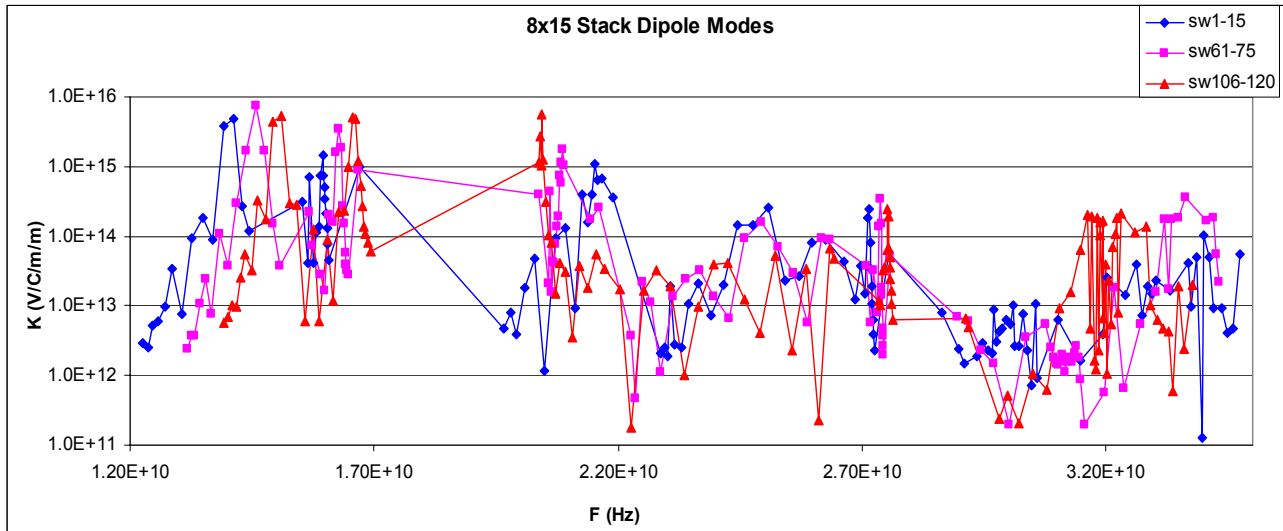
Dipole Mode Kick Factor



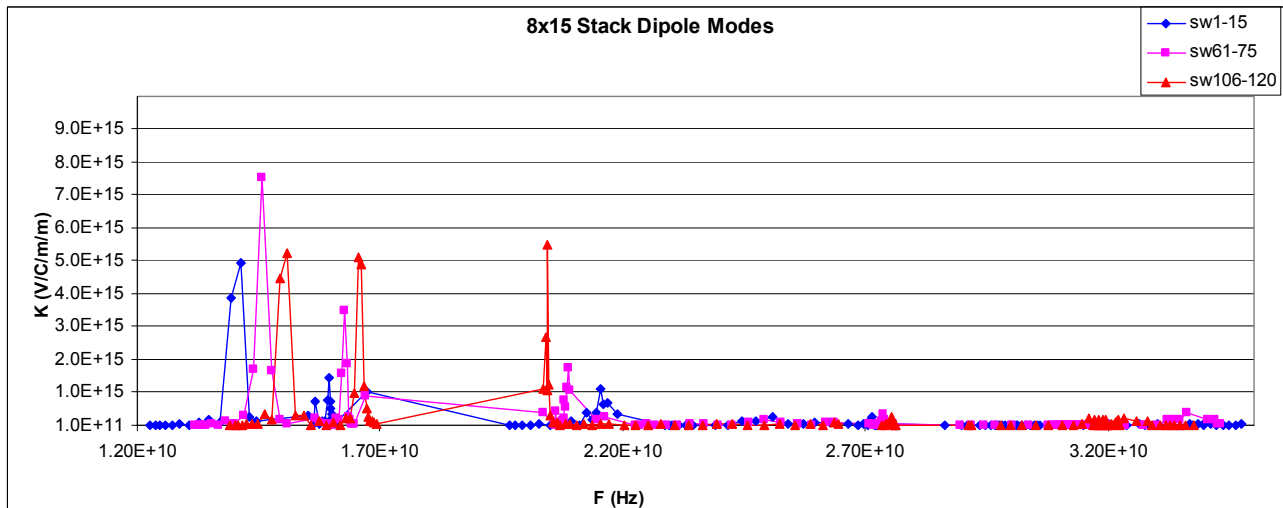
$$\Delta F = 8\% / 3.2\sigma$$



8x15 Stack Dipole Kick Factors



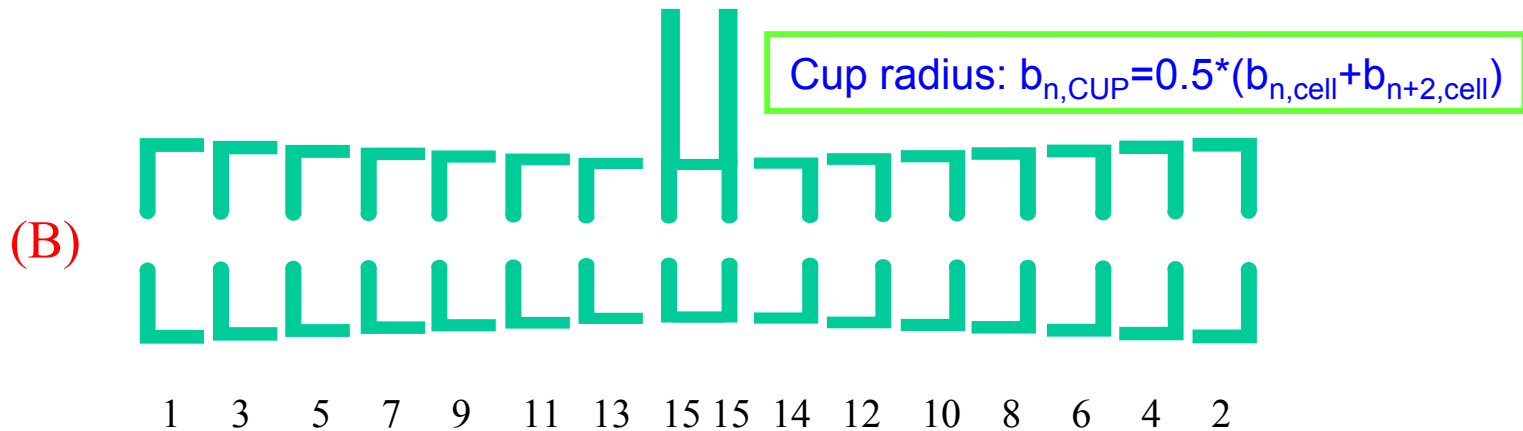
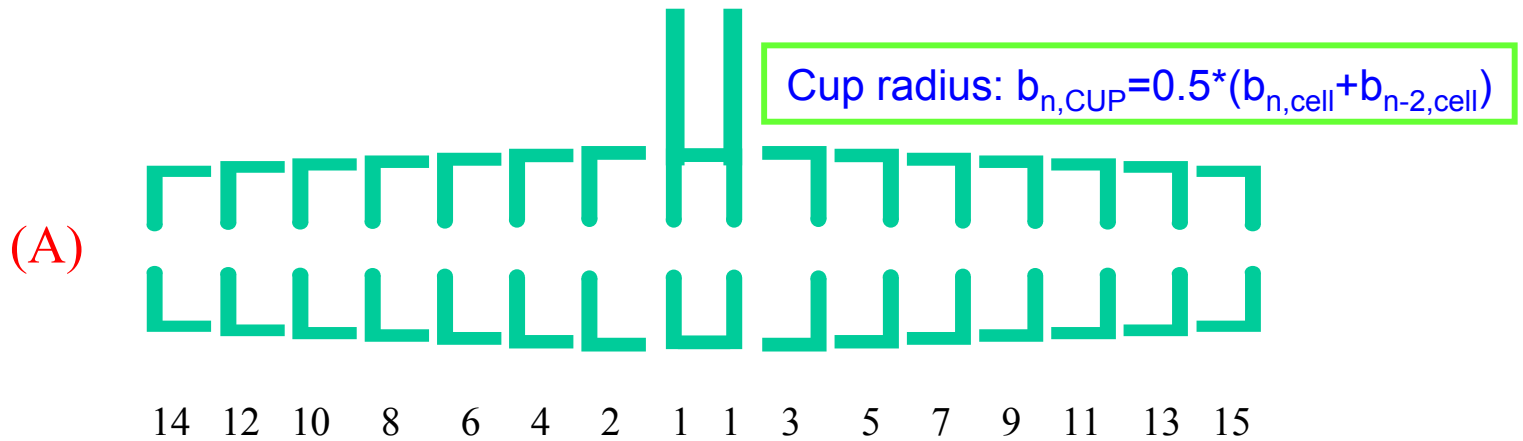
Log



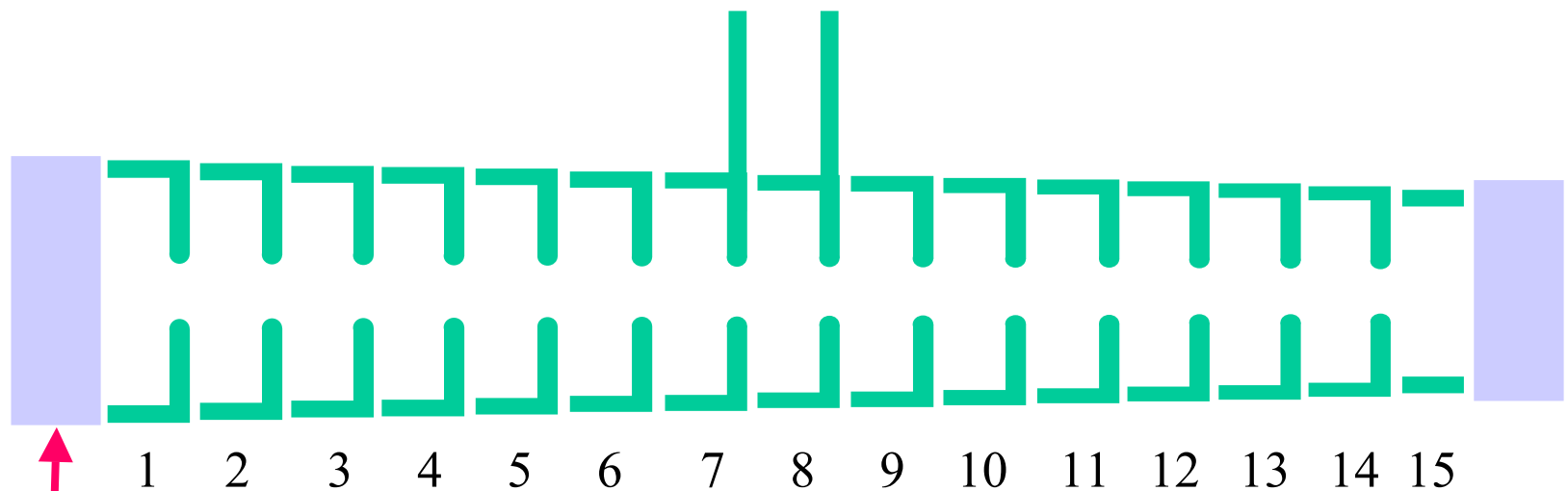
Linear

Detuned Standing Wave Structure (?)

Field Symmetric



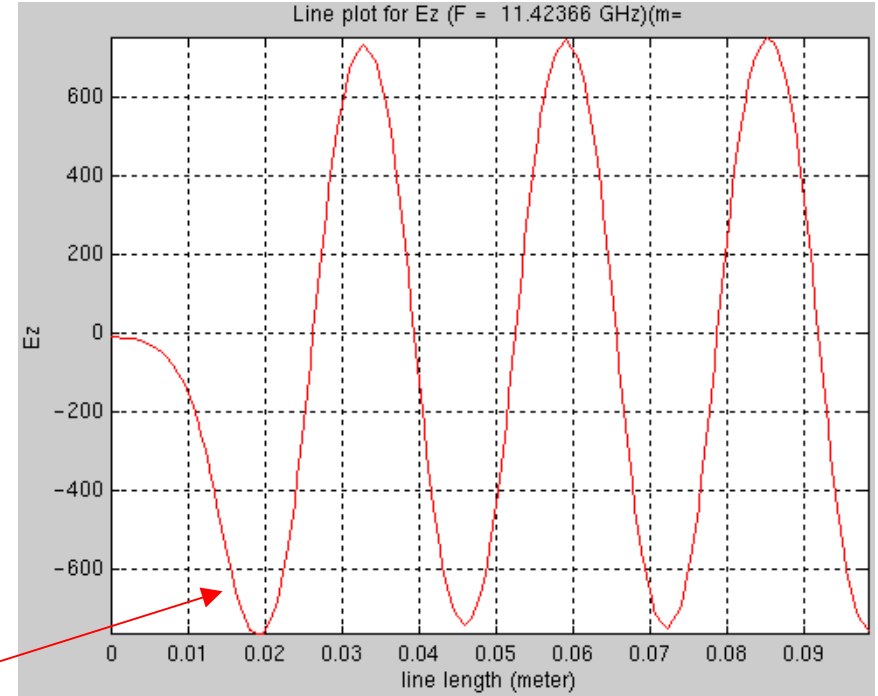
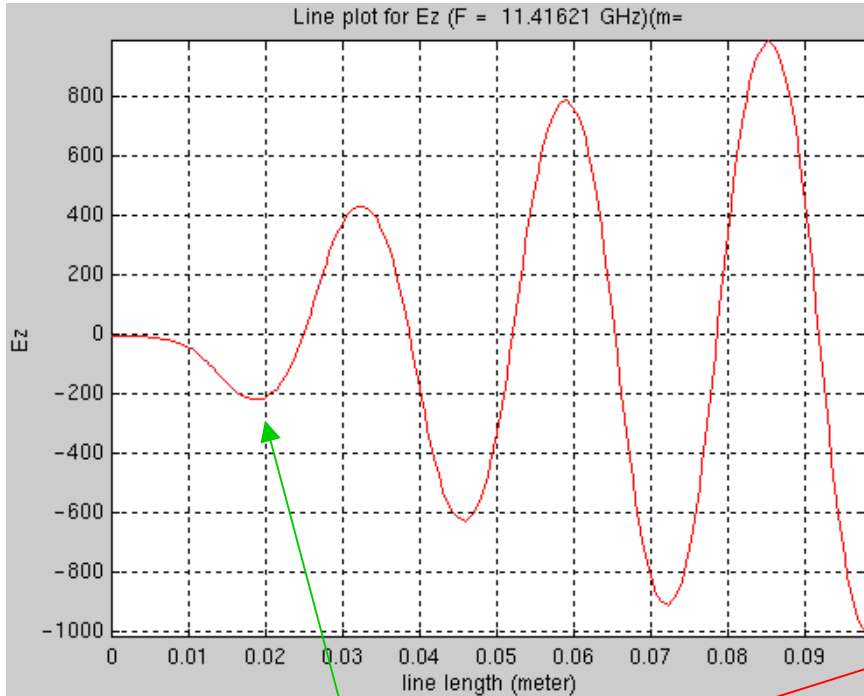
Detuned Standing Wave Structure Assembly



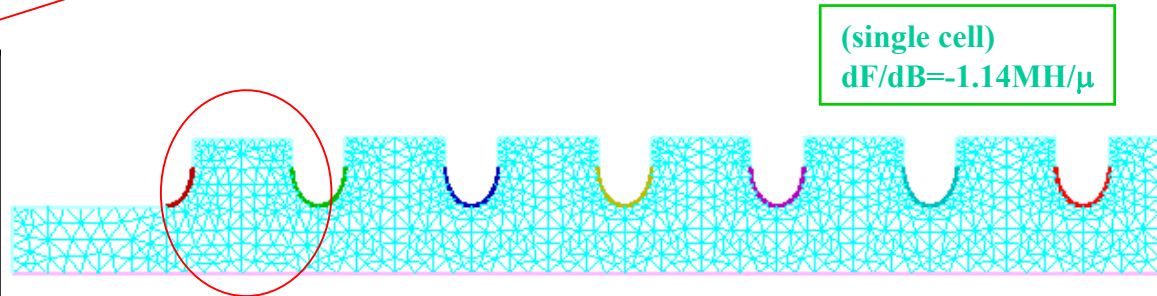
end piece: $a=a_{\text{cell30}}, t=t_{\text{cell30}}$

Cup radius: $b_{n,\text{CUP}}=0.5*(b_{n,\text{cell}}+b_{n-1,\text{cell}})$

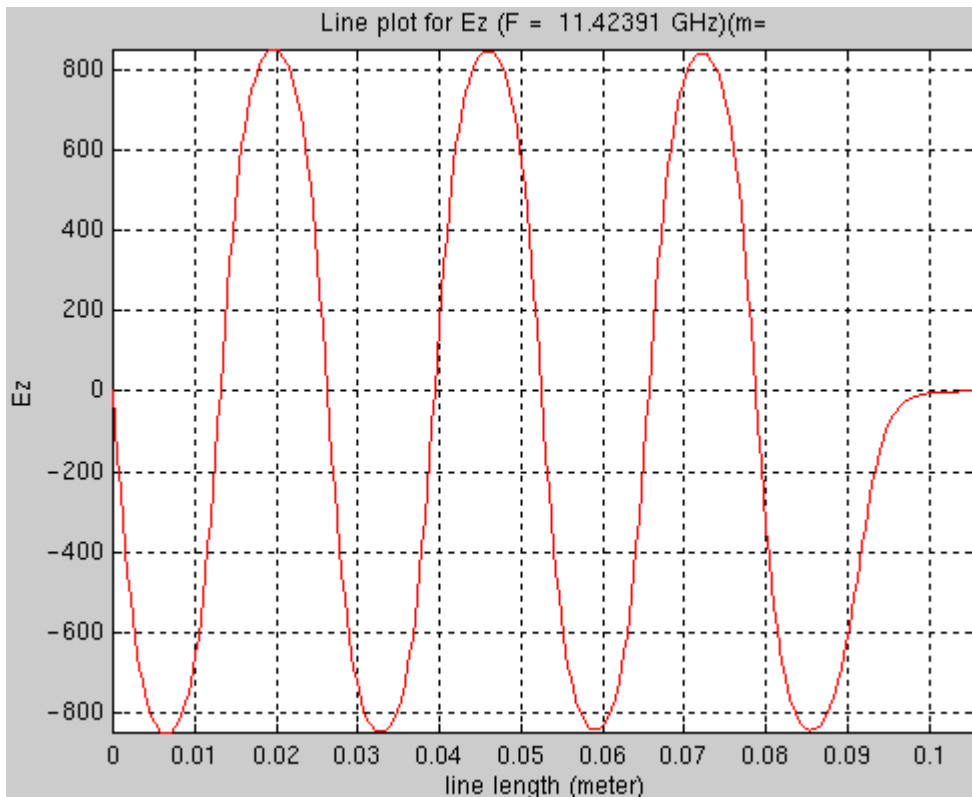
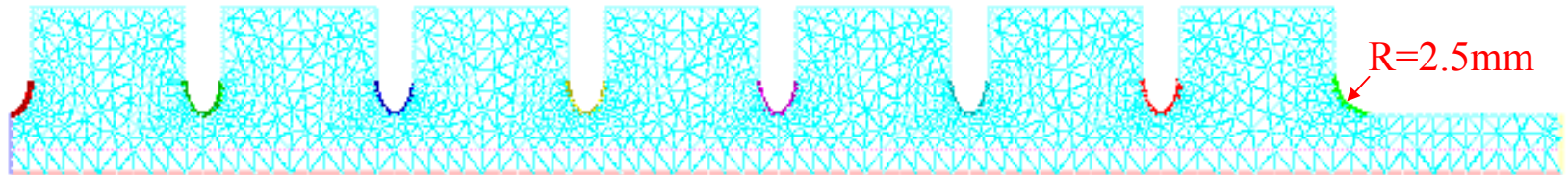
Flattening Field By Adjusting End-“b”



A	0.00565	0.00565
B (cell 1)	0.0115194	0.0113774
B (cell regular)	0.0115194	0.0115194
T	0.0046	0.0046
A_{nose}	0.0034	0.0034



Flattening Field By Adjusting End-plate

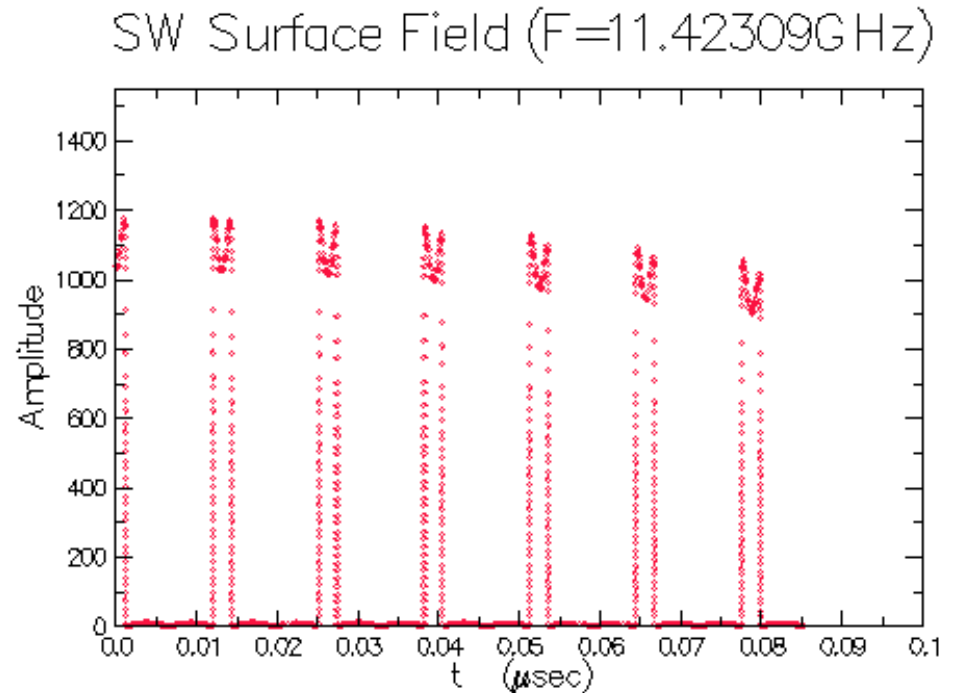
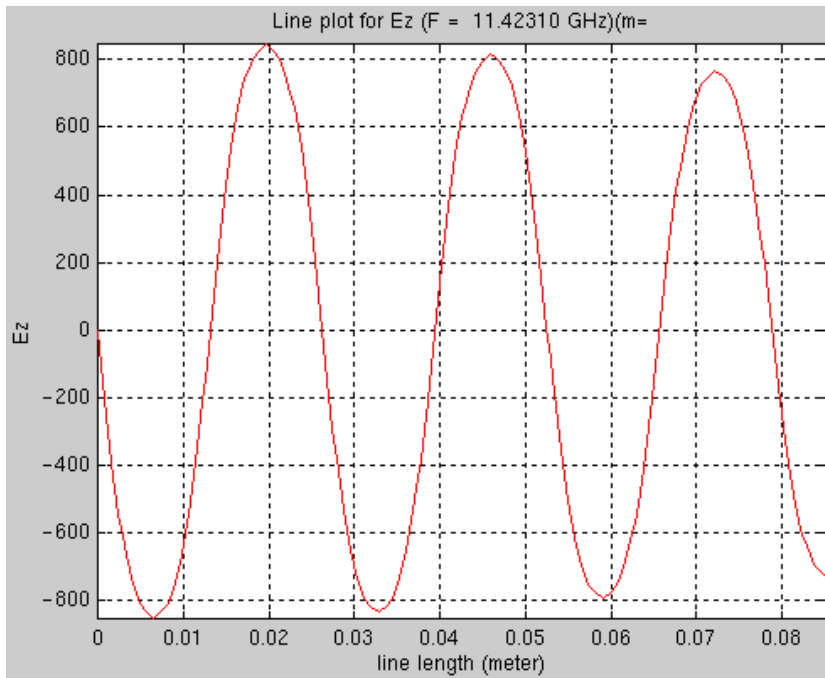


KEK SW20A375 Stack

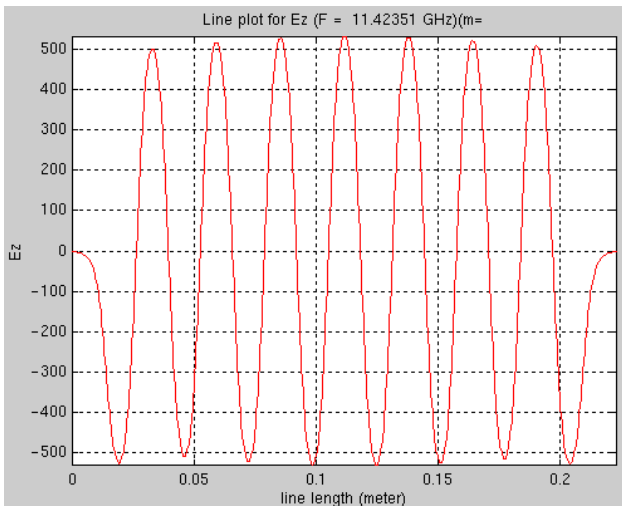
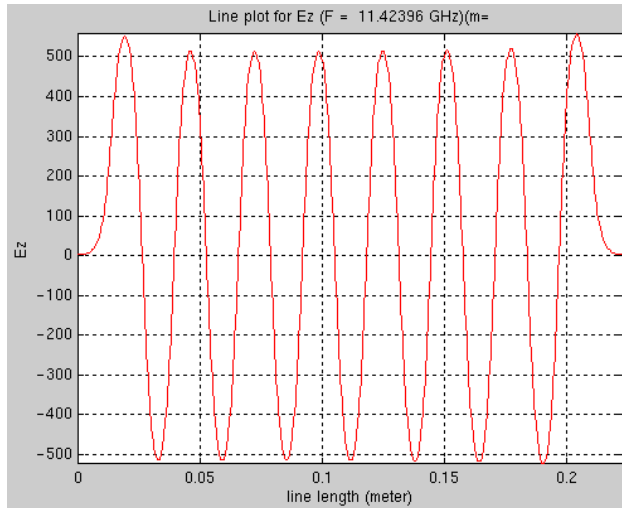
Parameters	SW20A375
a (mm)	3.75000
b (mm) (with square corners)	10.55666
t (mm)	2.6000
a _{nose} (mm)	2.2000
L (mm)	13.12117
R (MΩ/m)	81.92
Q	8621
Es/Ea	2.046
“b” with two r0.51mm fillets	10.56721
ZERO mode frequency	11.2247

Optimizing Field Profile

- Half of 15-cell stack
- Boundary:M-E
- “b” of coupler cell 10- μm larger



Simulation Of 15-cell Tapered Structure



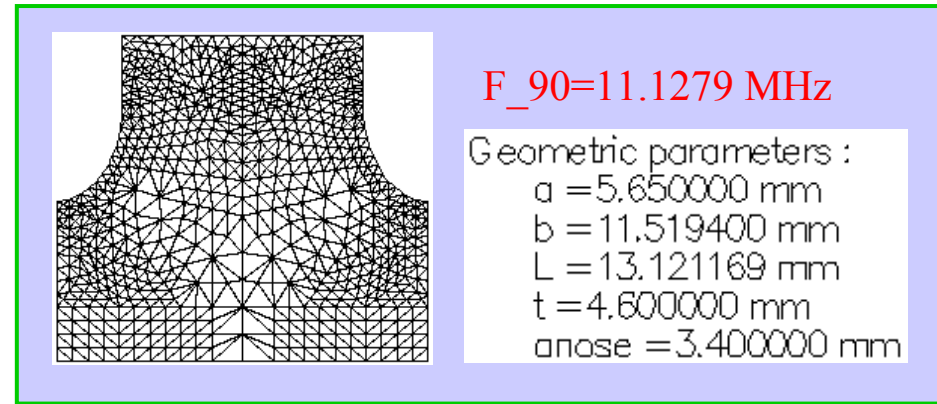
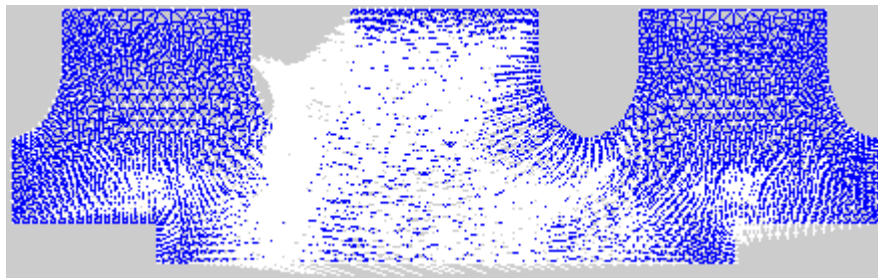
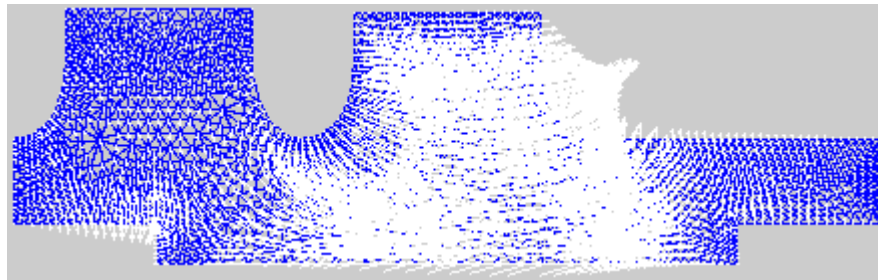
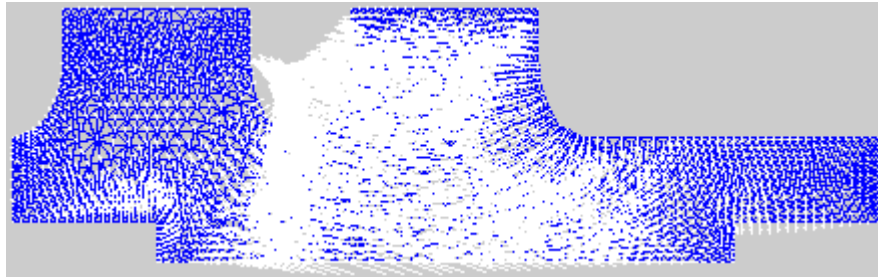
N	F1 (Hz)	a (mm)	b (mm)	t (mm)
0	1.42E+10	4.85462	10.87390	2.65200
1	1.42E+10	5.14991	10.83400	2.81487
2	1.42E+10	5.13882	11.00350	2.80825
3	1.43E+10	5.12785	10.99830	2.80174
4	1.43E+10	5.11700	10.99330	2.79534
5	1.43E+10	5.10627	10.98830	2.78904
6	1.43E+10	5.09565	10.98340	2.78285
7	1.43E+10	5.08502	10.97850	2.77669
8	1.43E+10	5.07450	10.97370	2.77063
9	1.43E+10	5.06411	10.96890	2.76468
10	1.43E+10	5.05384	10.96420	2.75883
11	1.43E+10	5.04355	10.95950	2.75300
12	1.43E+10	5.03324	10.95490	2.74720
13	1.43E+10	5.02320	10.95030	2.74157
14	1.43E+10	5.01300	10.94570	2.73589
15	1.43E+10	4.85462	10.80320	2.65200

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1	1.42E+10	5.14991	10.83700	2.81487
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10	1.43E+10	5.05384	10.96420	2.75883
11	1.43E+10	5.04355	10.95950	2.75300
12	1.43E+10	5.03324	10.95490	2.74720
13	1.43E+10	5.02320	10.95030	2.74157
14	1.43E+10	5.01300	10.94570	2.73589
15	1.43E+10	4.85462	10.80620	2.65200

Test SW (#1 of 4)
cell 1-15
R= 63 MΩ/m

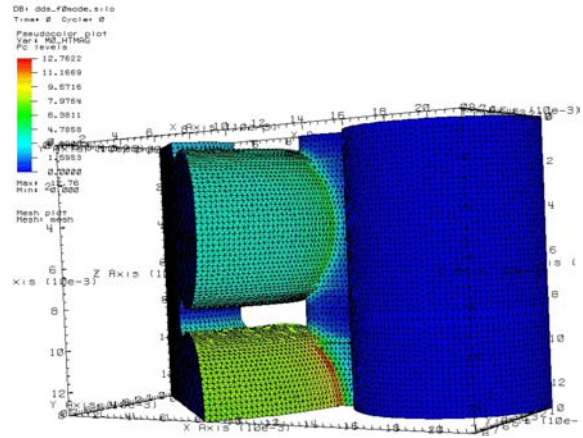
Flat field can be
obtained in
tapered structure

Plunger Measurement Simulation



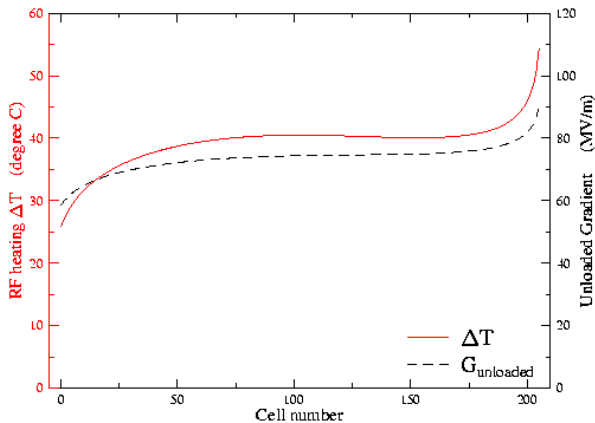
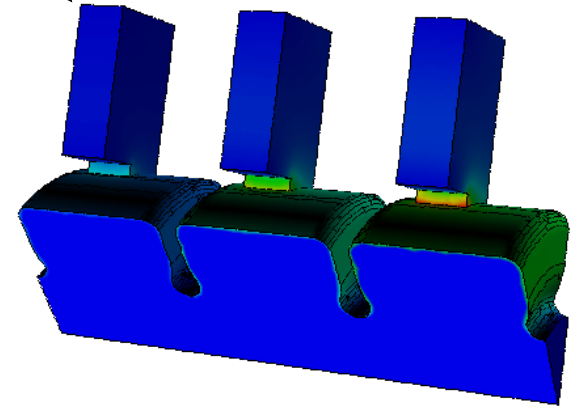
	Un-tuned	tuned	3 cell
$B_{\text{regular}}(\text{mm})$	11.5194	11.5194	11.5194
$B_{\text{end}}(\text{mm})$	11.5194	11.3774	11.5194
$F \text{ (MHz)}$	11.1228	11.2727	11.1311

Pulse Heating ($G=70\text{MV/m}$)



RDDS

MDDS



- Slots perturb current of accelerating mode. Current concentration at slots produce RF heating
- ΔT : RDDS1: $25^{\circ}\text{C} - 55^{\circ}\text{C}$; RDS : $<14^{\circ}\text{C}$